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Shirasa
3-30-01

Docket No. 8543-004-27 CIP

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: LIAO ET AL.

GAU: 2814 11/20/01
EXAMINER: QUACH, T.

SERIAL NO: 08/825,360

FILING DATE: MARCH 28, 1997

FOR: INTERCONNECT STRUCTURE FOR USE IN AN INTEGRATED CIRCUIT

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

This Amendment is submitted in answer to the Office Action dated September 26, 2000, which set a three-month period for response. A Request for Extension of Time for three months is attached hereto and incorporated herein by reference, thereby extending the date for response from December 26, 2000 to March 26, 2001.

Please amend the above-identified application as follows.

IN THE CLAIMS:

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21. (Amended) A method for forming a structure in an integrated circuit, said structure extending from a conductive surface through a channel having inner walls extending above said conductive surface, said method including the steps of:

- (a) depositing a layer of a refractory metal on said conductive surface and said inner walls of said channel;
- (b) forming a layer of a metal nitride on said layer of said refractory metal, wherein said layer of said metal nitride has a thickness extending from said layer of said refractory metal of less than 130 Å; and